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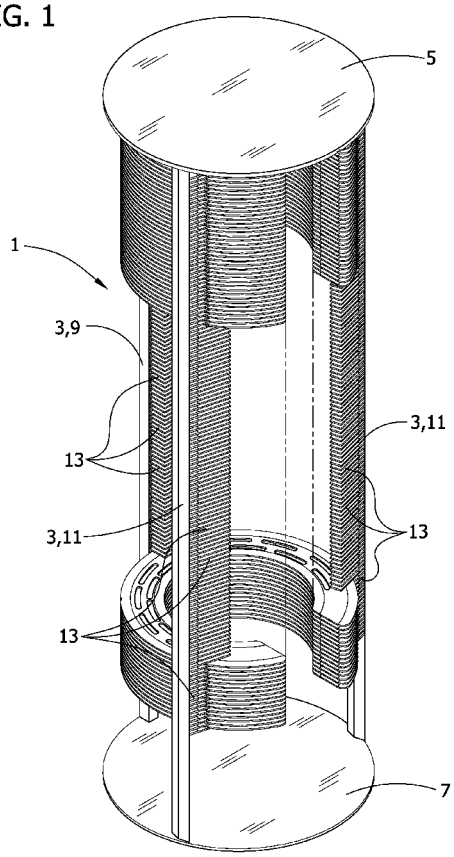
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(54) Title: LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT

FIG. 1



(57) Abstract: A support for a semiconductor wafer includes a plate having a support surface for supporting the wafer and a recessed surface spaced from the support surface and spaced from the wafer. A plurality of holes extends from the recessed surface, and the support surface is free of holes to inhibit contamination of the wafer.

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